

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	54	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:53
S2	0	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and "metal layer" and ("tantalum nitride" or "TaN") and depositon and argon and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S3	0	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and ("tantalum nitride" or "TaN") and depositon and argon and nitrogen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S4	35	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S5	15	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55
S6	4	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride" and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:55

S7	2	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride" and (argon near4 nitrogen)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 10:56
S8	2	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and chamber and metal and "tantalum nitride" and (argon near4 nitrogen) and deposit\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:41
S9	0	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and cap and liner and degass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:42
S10	0	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and degass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:42
S11	4	("ILD" or "interlevel dielectric") and etch\$4 and (open or via or hole or trench) and (semiconductor or wafer or substrate) and (inert near gas) and degas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/10 12:42